

1.0kV 4.0A HIGH VOLTAGE DIODE

HVRMx is high reliability resin molded type high voltage diode in small size package which is sealed a multilayered mesa type silicon chip by epoxy resin.

Features

- High speed switching
- High Current
- High surge resistivity for CRT discharge
- High reliability design
- High Voltage

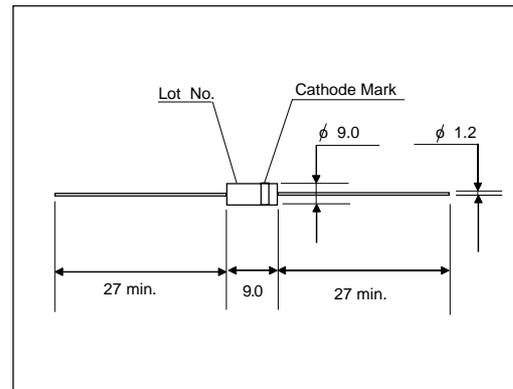
Applications

- X light Power supply
- Laser
- Voltage doubler circuit
- Microwave emission power

Maximum Ratings and Characteristics

- Absolute Maximum Ratings

Outline Drawings : mm



Cathode Mark

| Type | Mark |
|-------|------|
| HVRM1 | |

| Items | Symbols | Condition | HVRM1 | Units |
|--------------------------------------|-----------|---|-------------|--------------------|
| Repetitive Peak Reverse Voltage | V_{RRM} | | 1.0 | kV |
| Average Output Current | I_o | $T_a=25^{\circ}\text{C}$, Resistive Load | 4.0 | A _{peak} |
| Surge Current | I_{FSM} | | 100 | A _{peak} |
| Junction Temperature | T_j | | 155 | $^{\circ}\text{C}$ |
| Allowable Operation Case Temperature | T_c | | 125 | $^{\circ}\text{C}$ |
| Storage Temperature | T_{stg} | | -40 to +155 | $^{\circ}\text{C}$ |

- Electrical Characteristics ($T_a=25^{\circ}\text{C}$ Unless otherwise specified)

| Items | Symbols | Conditions | HVRM1 | Units |
|-------------------------------|----------|---|-------|---------------|
| Maximum Forward Voltage Drop | V_F | at 25°C , $I_F = I_{F(AV)}$ | 3.0 | V |
| Maximum Reverse Current | I_{R1} | at 25°C , $V_R = V_{RRM}$ | 50 | μA |
| | I_{R2} | at 100°C , $V_R = V_{RRM}$ | 500 | μA |
| Maximum Reverse Recovery Time | T_{rr} | at 25°C | --- | nS |
| Junction Capacitance | C_j | at 25°C , $V_R=0\text{V}$, $f=1\text{MHz}$ | -- | pF |